

# ISOCC 2011

Thursday-Friday, November 17-18, 2011  
Ramada Plaza Hotel, Jeju, Korea  
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## 2011 International SoC Design Conference



### Call for Papers



International SoC Design Conference (ISOCC) aims at providing the world's premier SoC design forum for leading researchers from academia and industries. Prospective authors are invited to submit papers of their original works. ISOCC 2011 is technically co-sponsored by **IEEE CAS** Society and accepted papers will be published on **IEEE Xplore**.



#### Paper Submission

Complete 2-page to 4-page manuscript (in Standard IEEE double-column format) is requested. Papers must be submitted electronically in PDF format. Only electronic submission will be accepted. For more information, please refer to the conference website: <http://www.isocc.org>.

#### Areas of Interest

Analog and Mixed-Signal Circuits	Communication SoCs
Display Driver and Imaging Devices	Embedded Memories
Embedded System Software	High Speed Signal Interfaces
Low Power Design Techniques	Microprocessor and DSP Architectures
Energy-Aware Systems	SoC Design Methodology
Multimedia (A/V) SoCs	SoCs for Automotive Technology
Wireline & Wireless ICs (RF ICs)	Sensor & MEMS
Signal Integrity/Interconnect Modeling	Power Electronics (Energy Harvesting)
SoC Testing and Verification	Bio & Medical Devices

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#### Chip Design Contest

Design contest provides the academia with the opportunity to introduce their novel chip designs to the real world. The selected designs will be awarded.

#### Best Paper Awards

The authors of selected papers will be awarded for technical contributions and their papers will be invited for publication in the Journal of Semiconductor Technology and Science (SCIE) published by Institute of Electronic Engineers of Korea (IEEK). (Visit [www.jsts.org](http://www.jsts.org) for submission details).

#### Important Dates

• <b>Deadline for submission of regular full paper;</b>	<b>21 Aug. 2011</b>
• <b>Deadline for submission of chip design contest ;</b>	<b>21 Aug. 2011</b>
• <b>Deadline for submission of special session full paper;</b>	<b>14 Sept. 2011</b>
• <b>Notification of acceptance (all submitted papers);</b>	<b>01 Oct. 2011</b>
• <b>Deadline for final paper submission;</b>	<b>15 Oct. 2011</b>
• <b>Deadline for author and early-bird registration;</b>	<b>15 Oct. 2011</b>

**28 Aug. 2011**

At least one author of each accepted paper must register by October 15, 2011.



- Design of Timing-Error-Resilient Systolic Arrays for Matrix Multiplication

Hsin-Chou Chi, Hsi-Che Tseng and Kun-Lin Tsai  
National Dong Hwa University, Taiwan

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08:20~09:50 Session 12

Room C

**Regular Session**

RF Techniques

Chair Yun Seong Eo  
(Kwangwoon University)

- A 10.3Gbps TransImpedance Amplifier with Mutually Coupled Inductors in 0.18- $\mu$ m CMOS  
Shigekazu Miyawaki<sup>(1)</sup>, Makoto Nakamura<sup>(2)</sup>, Akira Tsuchiya<sup>(1)</sup>, Keiji Kishine<sup>(3)</sup> and Hidetoshi Onodera<sup>(1)</sup>  
<sup>(1)</sup>Kyoto University, Japan  
<sup>(2)</sup>NTT Corporation, Japan  
<sup>(3)</sup>University of Shiga Prefecture, Japan

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- A Study on Wide-band Frequency Synthesizer for Advanced Wireless Communication  
Nakyoon Kim and Yong Moon  
Soongsil University, Korea

- A 5-Gb/s Low-Power Transmitter with Voltage-Mode Output Driver in 90nm CMOS Technology  
Jinsoo Rhim and Woo-Young Choi  
Yonsei University, Korea

- A 34 dBm IP<sub>0,1dB</sub> SOI SP3T Switch with an Integrated Negative-Bias Switch Controller at 2.4 GHz  
Sunwoo Yoon, JuYoung Jung and Dong-hyun Baek  
Chung-Ang University, Korea

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- Design Considerations for Cognitive Radio Based CMOS TV White Space Transceivers  
Jongsik Kim and Hyunchol Shin  
Kwangwoon University, Korea
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# A 5-Gb/s Low-Power Transmitter with Voltage-Mode Output Driver in 90nm CMOS Technology

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*Abstract*— A 5-Gb/s low-power transmitter having an output impedance calibration circuit and a voltage-mode output driver is implemented for high-speed serial link applications. The output impedance calibration circuit matches the output impedance of output driver to the characteristic impedance of the channel. This transmitter includes 32:1 serializer based on voltage-mode logic which operates successfully at 5-Gb/s. In addition, on-chip parallel PRBS7 ( $2^7-1$ ) generator is implemented for testing. The transmitter consumes 8.6mW with 300mVp-p output swing and occupies  $60 \mu\text{m} \times 70 \mu\text{m}$  of area.

*Keywords* - voltage-mode output driver; output-impedance calibration; low power; transmitter

## I. INTRODUCTION

For many interface applications, high-speed serial interface is widely used instead of parallel interface since it requires less area and power due to the reduced number of I/O pins and it suffers less from crosstalk noise and data-clock skew [1-3]. Furthermore, the need for power consumption reduction in high-speed serial interface circuits has greatly increased.

In this paper, a 5-Gb/s transmitter in 90nm CMOS technology is presented that has been designed for low-power consumption in mind. It employs voltage-mode output driver with output impedance calibration circuit in order to reduce the power of the transmitter while maintaining the output impedance matched to the channel. On-chip parallel PRBS generator and 32-to-1 serializer are also implemented.

Section II describes the overall design of the transmitter and the details of implemented circuits are shown in Section III. Section IV shows the experiment results.

## II. LOW POWER TRANSMITTER

### A. Overall structure

Figure 1 shows the overall block diagram of the transmitter. The PRBS generator produces 32 parallel PRBS-7 data streams of 156.25 Mb/s which are converted to 5-Gb/s serialized data by 32:1 serializer. Required multiple-rate clocks for the serializer are provided by the clock tree by dividing the external clock. The voltage-mode output driver consists of pre-driver and output driver with regulated supply voltage from output impedance calibration circuit. This calibration circuit

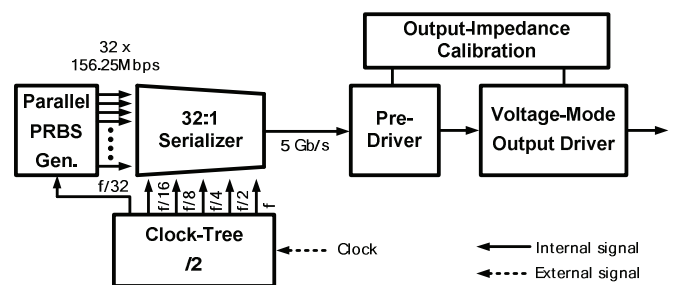


Fig. 1. Overall block diagram of transmitter

controls the output impedance of the output driver in order to minimize the reflection due to the impedance mismatch between output driver and the channel. All of the circuits including the output driver are designed based on voltage-mode logic to reduce the power consumption. The parallel PRBS generator is digitally synthesized.

### B. Voltage-mode logic and current-mode logic

The operation speed of voltage-mode logic has increased with the advanced CMOS technology. Compared to current-mode logic, which consumes constant power when the supply voltage is provided, voltage-mode logic consumes power only during data transitions. Since the amount of leakage current is less than the dynamic current for over 65nm CMOS technology, the power consumption of the voltage-mode logic is much less than that of current-mode logic. Moreover, the transistor size for voltage-mode logic can be smaller than that of current-mode logic due to its smaller current usage, which consequentially reduces the overall circuit area.

### C. Voltage-mode output driver

Output driver designed with current-mode logic is shown in Figure 2. It can easily match the output impedance by controlling the load resistor or bias voltage applied to PMOS transistors. Furthermore, the maximum operation speed of current-mode logic is larger than that of voltage-mode logic. However, it consumes a considerable amount of power in order to drive the load resistor, particularly at the last stage of the output driver where the load resistance is the characteristic

impedance of the channel. Usually, output driver based on current-mode logic consumes over 10mW of power, which is much more than desired for low-power interface systems. The output driver based on voltage-mode logic consumes much less power and occupies less area as well. The difficulty of using voltage-mode logic for output driver is matching the driver output impedance to the channel. In this case, the output impedance is determined by the supply voltage and the gate voltages applied to the composing transistors. Consequently, regulation of the supply voltage as well as pre-driver is necessary.

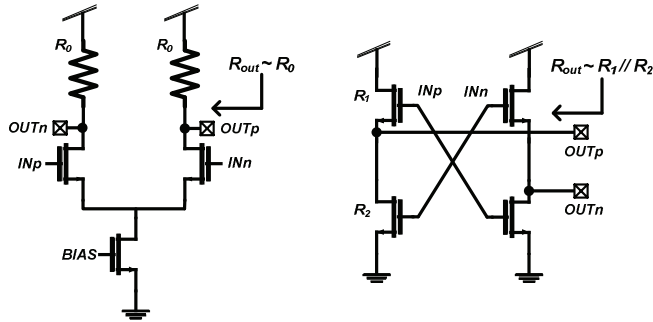


Fig. 2. Current-mode logic (left) and voltage-mode logic (right)

### III. CIRCUIT IMPLEMENTATION

The voltage-mode logic adopted in this work is based on clocked inverter and pass-gate multiplexer as shown in figure 3. The clocked inverter keeps the data if the pass gates are turned off and inverts the input data if otherwise. The pass-gate multiplexer chooses its output according to the clock input.

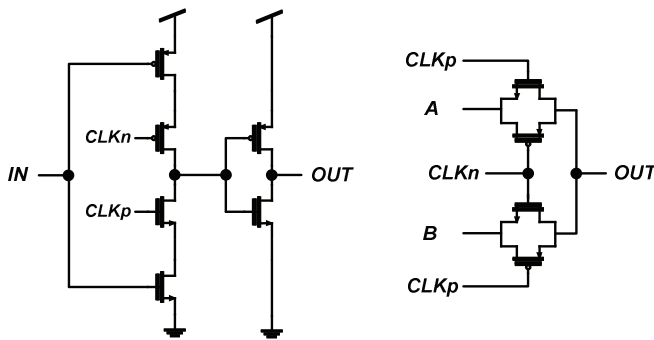


Fig. 3. Clocked inverter (left) and pass-gate multiplexer (right)

#### A. 32:1 Serializer

As shown in the figure 4, 32:1 serializer includes several 2:1 serializers, and each 2:1 serializer is composed of two latches and 2:1 multiplexers (MUXs). The dividers are used for the clock tree in order to provide proper clock signals to 32:1 serializer. Figure 5 and 6 show the schematic of the 2:1 serializer. Each 2:1 serializer is based on a double-edge triggered flip-flop [5], including 2 latches and 1 multiplexer, and one additional latch is inserted to generate half-period delay. Two latches keep the data alternatively by using the

opposite clock. The 2:1 multiplexer finally serializes two input data using both edges of the clock.

In order to generate differential signal for output driver, the last stage of 32:1 serializer uses the pseudo-differential signaling scheme. Figure 6 shows the schematic of the pseudo-differential 2:1 serializer, which occupies additional 2:1 multiplexer with cross-coupled input data at the end of the stage.

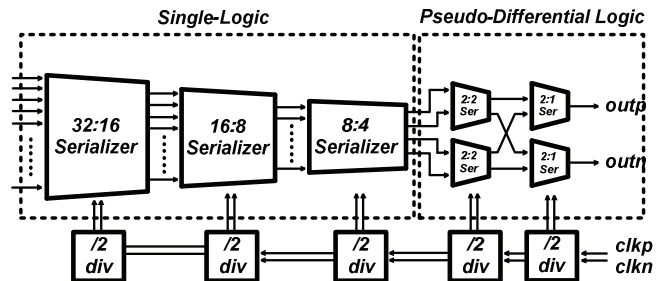


Fig. 4. 32:1 Serializer

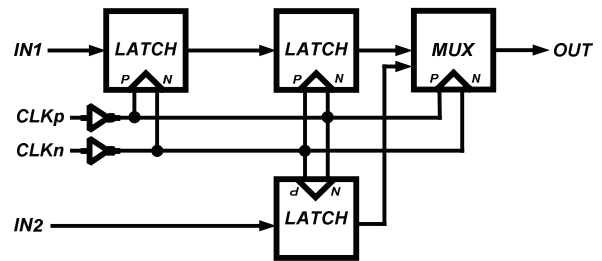


Fig. 5. 2:1 Serializer

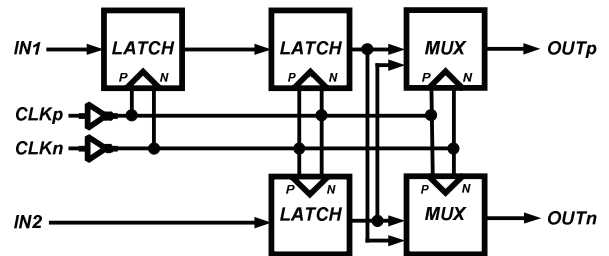


Fig. 6. 2:1 Serializer with pseudo-differential output

#### B. Impedance Calibration of Voltage-mode Output Driver

The voltage-mode output driver with output impedance calibration circuit is implemented. As mentioned above, the voltage-mode output driver uses less power compared to the output driver based on current-mode logic. Output driver based on current-mode logic should be able to drive relatively low impedance in order to match the characteristic impedance of the channel. Meanwhile, it is difficult to match the output impedance to the characteristic impedance of the channel. Therefore, the output impedance calibration circuit is also designed for this transmitter.

The voltage-mode output driver consists of two parts: the pre-driver and the output driver. The pre-driver is an inverter stage with regulated supply voltage which matches the output impedance of the driver to the characteristic impedance of the channel. The output driver has two complementary pairs of NMOS transistors.

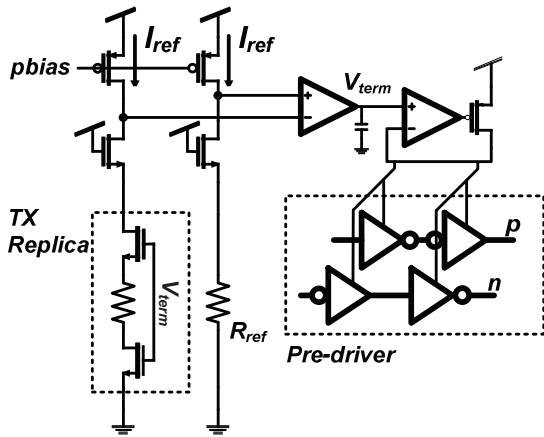


Fig. 7. Supply regulation on pre-driver

The impedance calibration circuit for the pre-driver is shown in figure 7. It is a negative feedback loop including reference resistor ( $R_{ref}$ ), which represents the characteristic impedance of the channel, and a replica output driver. Two PMOS transistors drive the same amount of current ( $I_{ref}$ ) to  $R_{ref}$  and the replica of output driver. The feedback loop forces the gate voltage of the output driver replica ( $V_{tern}$ ) in order to make the impedance of the output driver replica equal to  $R_{ref}$ . Thus, the output impedance of output driver becomes  $R_{ref}$  by regulating the supply voltage of the pre-driver to  $V_{tern}$ .

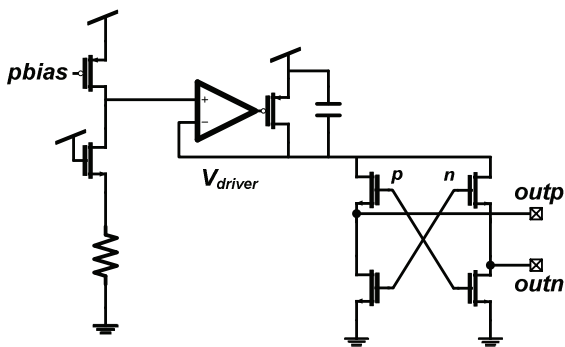


Fig. 8. Supply regulation on output driver

The power of output driver should be also regulated to match the output impedance to  $R_{ref}$  as shown in figure 8. The second regulator, which generates the supply voltage of output driver ( $V_{driver}$ ), is designed by adopting the same structure used for pre-driver supply regulation. With the regulated supply voltage ( $V_{driver}$ ) and pre-driver input ( $V_{tern}$ ), the output impedance of the output driver can be matched to  $R_{ref}$ .

#### IV. MEASUREMENT RESULTS

The transmitter is implemented with 90nm CMOS technology and measured with on-wafer probing. The microphotograph of the fabricated chip is shown in figure 9. The area of the transmitter core is  $60 \mu\text{m} \times 70 \mu\text{m}$ . It produces 5-Gb/s data with  $17.73\text{ps}_{p2p}$  of jitter under 1.2V supply voltage and consumes 8.5mW of power. The measurement setup is shown in figure 10 and the eye-diagram of the data is shown in figure 11.

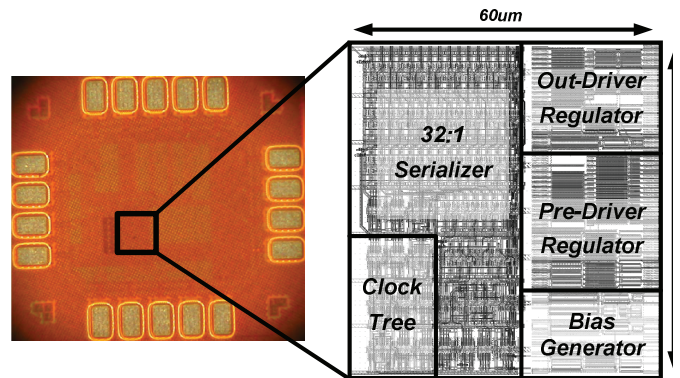


Fig. 9. Microphotograph and layout of fabricated chip

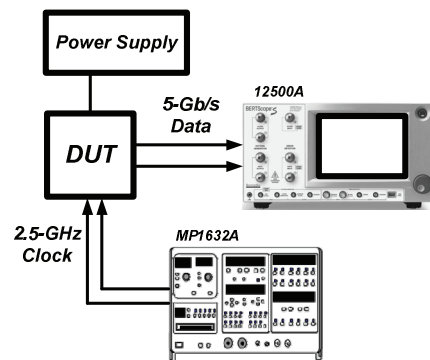


Fig. 10. Measurement setup

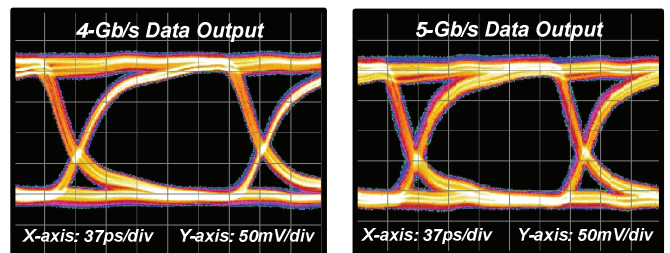


Fig. 11. Eye-diagram of output data: @ 4-Gb/s (left) @ 5-Gb/s (right)

The operation of output-impedance calibration circuit is verified by measuring the reflection coefficient of the transmitter and the output impedance. The S11 parameter in figure 12 is lower than  $-30\text{dB}$  at 2.5GHz and the output impedance in figure 13 is located at the center of the Smith chart. Table 1 summarizes the performance of designed transmitter

## V. CONCLUSION

A 5-Gb/s transmitter with voltage mode output driver is presented in this paper. This transmitter includes PRBS generator, 32:1 serializer and output impedance calibration circuit. It is fabricated in 90nm CMOS technology based on voltage-mode logic. It consumes 8.5mW of power at 5-Gb/s of data-rate and occupies 60  $\mu\text{m}$  X 70  $\mu\text{m}$  of area. The transmitter generates 5-Gb/s data with 17.73ps of jitter. The operation of output impedance calibration circuit has been verified by measuring the reflection and the output impedance of the output driver.

## ACKNOWLEDGMENT

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## REFERENCES

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- [5] Jri Lee and Behzad Razavi, "A 40-Gb/s Clock and Data Recovery Circuit in 0.18 $\mu\text{m}$  CMOS Technology," *IEEE Journal of Solid-State Circuits*, Vol. 38, issue 12, pp. 2181-2190, Dec. 2003.

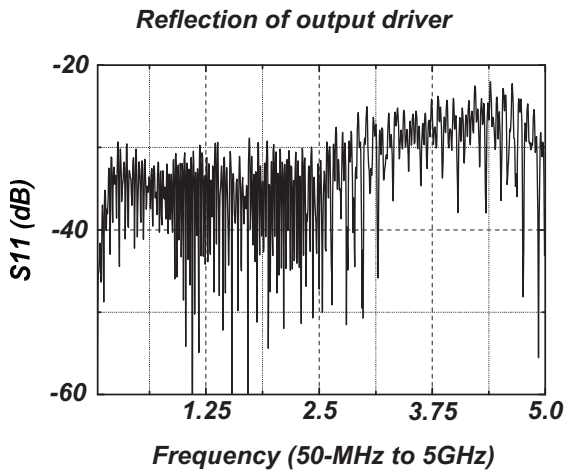


Fig. 12. Measured reflection of voltage-mode output driver

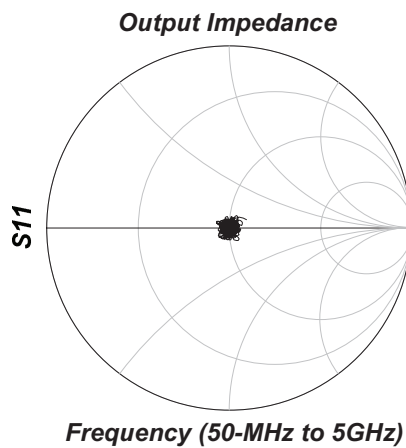


Fig. 13. Measured output impedance of voltage-mode output driver

TABLE I. PERFORMANCE SUMMARY

<i>Low Power Transmitter</i>	
Technology	90nm CMOS
Supply Voltage	1.2 V
Data-rate	Max. 5-Gb/s
Power Consumption	8.5mW @ 5-Gb/s
Power Efficiency	1.72 mW/Gb/s
Area	60 $\mu\text{m}$ X 70 $\mu\text{m}$ (Excluding capacitor)
Jitter	17.73psp2p (0.088UI)